

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

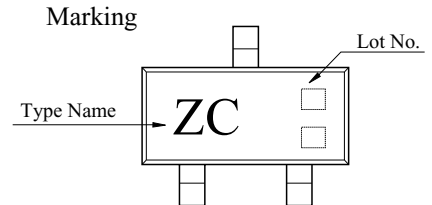
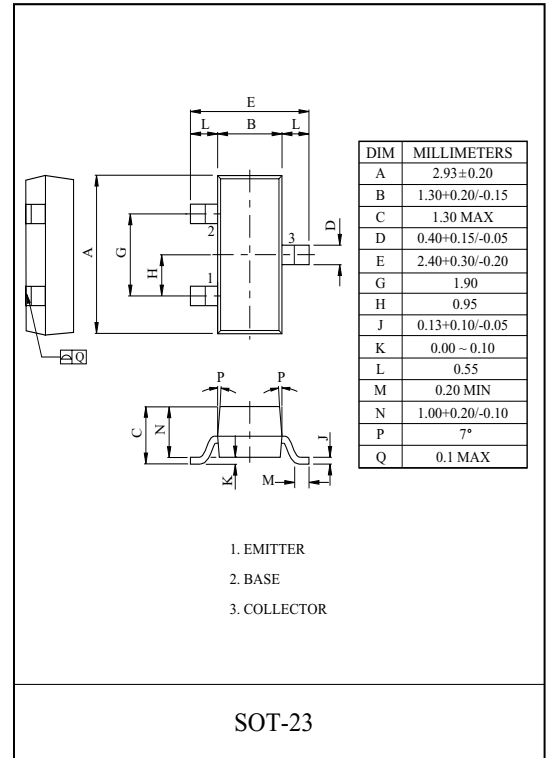
FEATURES

- Low Leakage Current
: $I_{CEX}=50nA(\text{Max.}), I_{BL}=50nA(\text{Max.})$
@ $V_{CE}=30V, V_{EB}=3V$.
- Excellent DC Current Gain Linearity.
- Low Saturation Voltage
: $V_{CE(\text{sat})}=0.3V(\text{Max.}) @ I_C=50mA, I_B=5mA$.
- Low Collector Output Capacitance
: $C_{ob}=4pF(\text{Max.}) @ V_{CB}=5V$.
- Complementary to 2N3906S.

MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	200	mA
Base Current	I_B	50	mA
Collector Power Dissipation	P_C^*	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

* PC : Package Mounted On 99.5% Alumina 10 × 8 × 0.6mm)



2N3904S

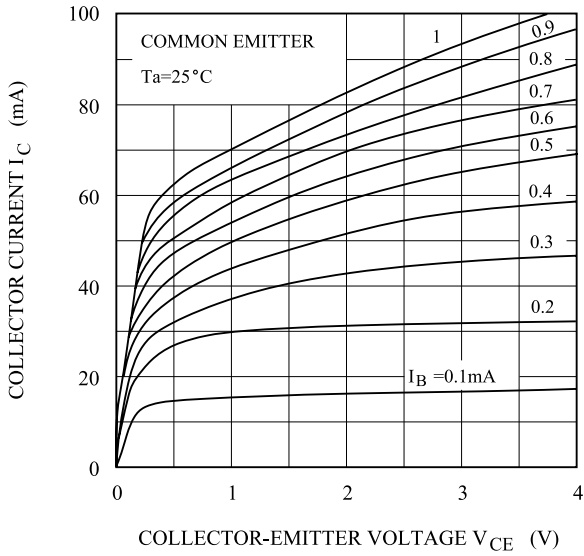
ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CEX}	$V_{CE}=30V, V_{EB}=3V$	-	-	50	nA
Base Cut-off Current		I_{BL}	$V_{CE}=30V, V_{EB}=3V$	-	-	50	nA
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	60	-	-	V
Collector-Emitter Breakdown Voltage *		$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	40	-	-	V
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6.0	-	-	V
DC Current Gain	*	$h_{FE(1)}$	$V_{CE}=1V, I_C=0.1mA$	40	-	-	
		$h_{FE(2)}$	$V_{CE}=1V, I_C=1mA$	70	-	-	
		$h_{FE(3)}$	$V_{CE}=1V, I_C=10mA$	100	-	300	
		$h_{FE(4)}$	$V_{CE}=1V, I_C=50mA$	60	-	-	
		$h_{FE(5)}$	$V_{CE}=1V, I_C=100mA$	30	-	-	
Collector-Emitter Saturation Voltage *	*	$V_{CE(sat)1}$	$I_C=10mA, I_B=1mA$	-	-	0.2	V
		$V_{CE(sat)2}$	$I_C=50mA, I_B=5mA$	-	-	0.3	
Base-Emitter Saturation Voltage *	*	$V_{BE(sat)1}$	$I_C=10mA, I_B=1mA$	0.65	-	0.85	V
		$V_{BE(sat)2}$	$I_C=50mA, I_B=5mA$	-	-	0.95	
Transition Frequency		f_T	$V_{CE}=20V, I_C=10mA, f=100MHz$	300	-	-	MHz
Collector Output Capacitance		C_{ob}	$V_{CB}=5V, I_E=0, f=1MHz$	-	-	4.0	pF
Input Capacitance		C_{ib}	$V_{BE}=0.5V, I_C=0, f=1MHz$	-	-	8.0	pF
Input Impedance		h_{ie}	$V_{CE}=10V, I_C=1mA, f=1kHz$	1.0	-	10	k
Voltage Feedback Ratio		h_{re}		0.5	-	8.0	$\times 10^{-4}$
Small-Signal Current Gain		h_{fe}		100	-	400	
Collector Output Admittance		h_{oe}		1.0	-	40	μ
Noise Figure		NF		$V_{CE}=5V, I_C=0.1mA, R_g=1k\Omega, f=10Hz \sim 15.7kHz$	-	-	5.0
Switching Time	Delay Time	t_d		-	-	35	nS
	Rise Time	t_r		-	-	35	
	Storage Time	t_{stg}		-	-	200	
	Fall Time	t_f		-	-	50	

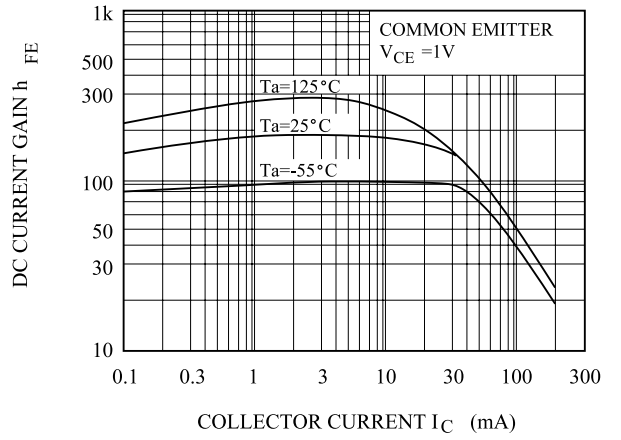
* Pulse Test : Pulse Width 300 μ s, Duty Cycle 2%.

2N3904S

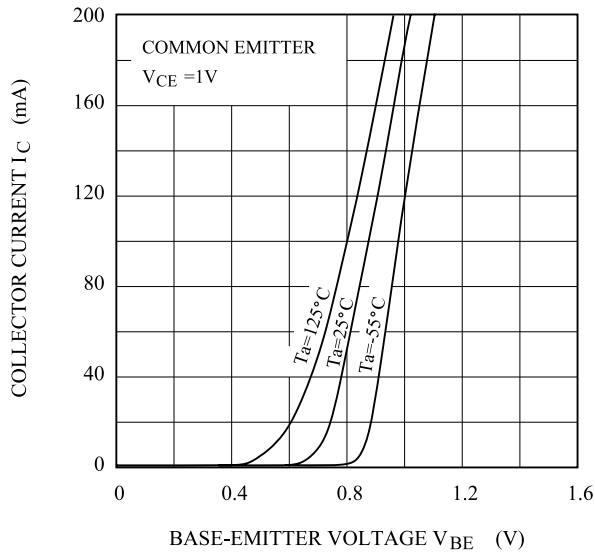
$I_C - V_{CE}$



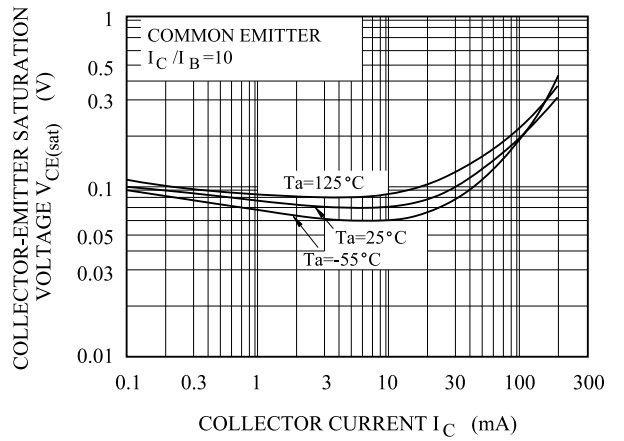
$h_{FE} - I_C$



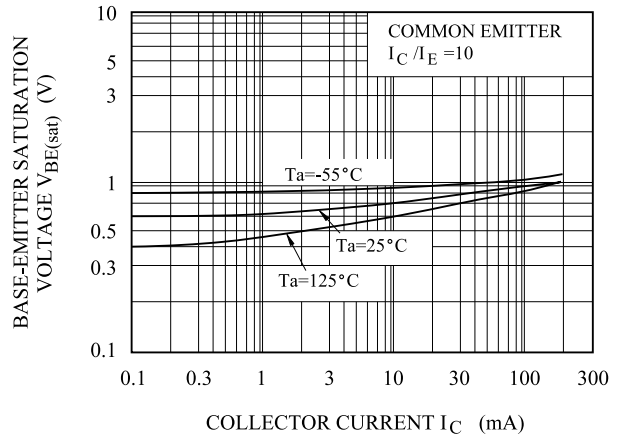
$I_C - V_{BE}$



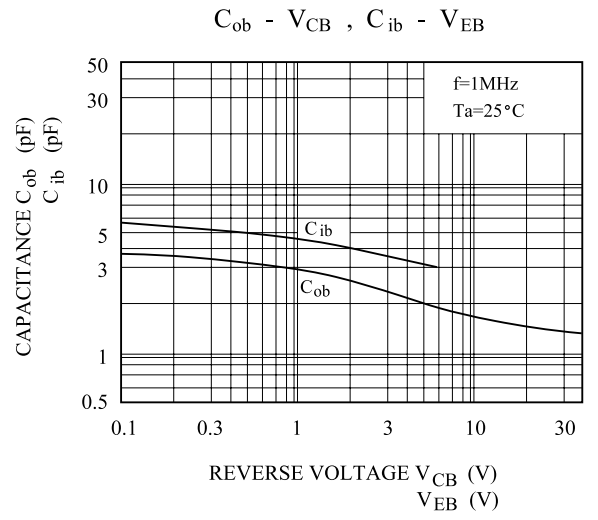
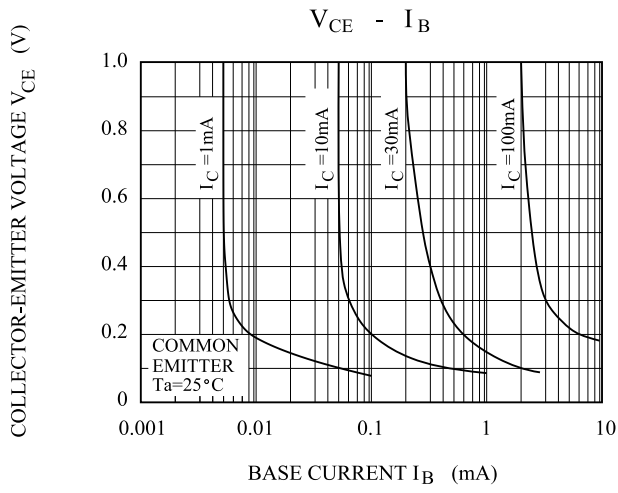
$V_{CE(sat)} - I_C$



$V_{BE(sat)} - I_C$



2N3904S



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - BJT category](#):

Click to view products by [KEC manufacturer](#):

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [BC557/116](#) [BSW67A](#) [NJVMJD148T4G](#) [NTE123AP-10](#) [NTE153MCP](#) [NTE16](#)
[NTE195A](#) [NTE92](#) [C4460](#) [2N4401-A](#) [2N6728](#) [2SA1419T-TD-H](#) [2SA2126-E](#) [2SB1204S-TL-E](#) [2SC2712S-GR,LF](#) [2SC5488A-TL-H](#)
[2SD2150T100R](#) [SP000011176](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SC2412KT146S](#) [2SD1816S-TL-E](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#)
[MJE340](#) [US6T6TR](#) [NJL0281DG](#) [732314D](#) [CPH3121-TL-E](#) [CPH6021-TL-H](#) [873787E](#) [IMZ2AT108](#) [UMX21NTR](#) [MCH6102-TL-E](#)
[NJL0302DG](#) [2N3583](#) [30A02MH-TL-E](#) [NSV40301MZ4T1G](#) [NTE13](#) [NTE26](#) [NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [STX83003-AP](#)